

Dear colleagues, we kindly invite you to a lecture of

Prof. Enrique Miranda

Universitat Autònoma de Barcelona, Spain

Compact modeling of hysteresis effects in RRAM devices

Abstract: Resistive switching (RS) is called to be the next breakthrough in the field of memory devices. Devices based on this physical mechanism, also called resistive RAMs, can, under an appropriate electrical, physical or chemical stimulus, reversibly change their resistance state and retain this value even when the power is turned off. This is a nonvolatile effect which replaces the charge storage mechanism used by conventional memory devices. RRAM can also be applied in logic and neuromorphic circuits. In this seminar I will focus the attention on recent and past findings relating RS with quantum phenomena and on the implementation of a compact model using the theory of memristive systems.

Seminar will take place on Friday 7/4/2017 at 10.00 in the seminar room of IEE (Rm. 101).